

## Transport and Magnetic Properties of $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$ Manganites

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We present here the effect of Al doping on structural, electrical and magnetic properties in  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) manganites. Al has been doped on its Mn site because it has no magnetic moment and its atomic radius is smaller than that of Mn. X-ray diffraction (XRD) pattern confirms the single phase character of both the samples with orthorhombic symmetry and space group *Pnma*. No structural change has been observed due to Al doping up to  $x = 0.1$  except the decrease in lattice parameters. Dc conductivity data have been analyzed using different conduction mechanisms. Theoretical models fitting show that the high temperature ( $T > \Theta_D/2$ ,  $\Theta_D$  being the Debye temperature) dc conductivity ( $\sigma_{dc}$ ) of these samples is due to adiabatic large polaron-hopping conduction. The value of polaron coupling constant, which is a measure of electron-phonon (e-ph) interaction, suggests the presence of strong e-ph interaction in  $x = 0.1$  sample. It is observed that ferromagnetism (FM) decreases with Al doping. Minimum value of magnetization is obtained for  $x = 0.1$  sample.

**Key Words:** Electrical Properties, Magnetic materials

### INTRODUCTION

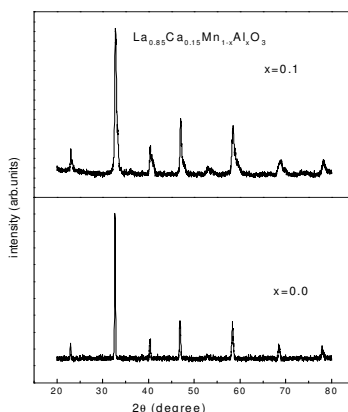
Observation of colossal magnetoresistance (CMR) in the perovskite manganite system of the form  $\text{R}_{1-x}\text{A}_x\text{MnO}_3$  (R= rare earth, A= Ca, Sr, Ba, Pb, etc) has spurred considerable interest in the study of these compounds among the scientific community.<sup>1</sup> These materials show a close interplay among the spin, charge and orbital ordering.<sup>2</sup> Nature of ferromagnetic insulating (FMI) state in lightly doped  $\text{R}_{1-x}\text{A}_x\text{MnO}_3$  ( $x = 0.1 - 0.2$ ) rare earth manganite perovskite system continues to pose a complex problem.<sup>3</sup> Particularly, FMI  $\text{La}_{0.85}\text{Ca}_{0.15}\text{MnO}_3$  perovskite has been studied extensively because of its complex  $\text{Mn}^{3+}$ -O- $\text{Mn}^{4+}$  network.<sup>3</sup> Despite the exhaustive study of the effect of the rare earth replacement in these manganites, very little is known about FMI state.<sup>4</sup> The present article puts forward the structural, dc conductivity and magnetization studies of the Al substituted  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) samples.

## EXPERIMENTAL

Polycrystalline bulk samples of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  (LCMAO) ( $x = 0.0$  and  $0.1$ ) were prepared by standard solid-state reaction route using  $\text{La}_2\text{O}_3$ ,  $\text{CaCO}_3$ ,  $\text{MnO}_2$ , and  $\text{Al}_2\text{O}_3$ . The stoichiometric mixture was heated at  $500^\circ\text{C}$  for 2 h, at  $800^\circ\text{C}$  for 24 h and at  $900^\circ\text{C}$  for 12 h in a closed Muffle furnace. Then it is pelletized and sintered at  $1150^\circ\text{C}$  for 24 h. Powder x-ray diffraction (XRD) are performed using Bruker D8 X-ray diffractometer with  $\text{CuK}\alpha$  radiation at room temperature. DC resistivity of the samples is measured by conventional four-probe method in the temperature range 80-300 K. Magnetization as a function of applied magnetic field (0-8T) at fixed temperature is measured using PPMS-Vibrating Sample Magnetometer (VSM) of Quantum Design.

## RESULTS AND DISCUSSION

Figure 1 shows the XRD pattern of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) samples which show the clean and single phase. The lattice parameters were calculated using the PowderX software. It is found that the lattice parameter  $a$

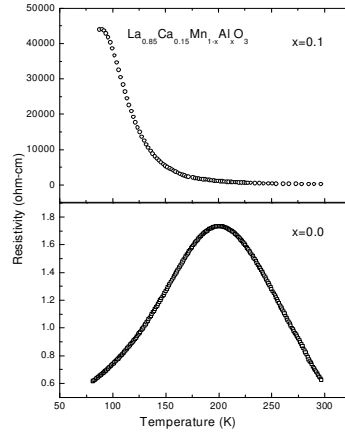


**Fig.1.** Room temperature x-ray diffraction (XRD) pattern for  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) samples.  $a$  decreases from  $5.477$  to  $5.425 \text{ \AA}$ ,  $b$  from  $7.754$  to  $7.730 \text{ \AA}$  and  $c$  from  $5.511$  to  $5.491 \text{ \AA}$  with Al substitution at Mn site. The unit cell volume decreases from  $234.065$  to  $231.412 \text{ \AA}^3$  due to Al doping and is consistent with the lower size of  $\text{Al}^{3+}$  ( $0.5 \text{ \AA}$ ) compared to that of  $\text{Mn}^{3+}$  ( $0.6 \text{ \AA}$ ). Figure 2 shows the resistivity ( $\rho$ ) of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  samples as a function of temperature (80-300K). Room temperature ( $\sim 300 \text{ K}$ ) resistivity for  $\text{La}_{0.85}\text{Ca}_{0.15}\text{MnO}_3$  sample is  $\sim 0.62 \text{ } \Omega \text{ cm}$ , whereas that for Al doped samples with  $x = 0.1$ , is  $\sim 105 \text{ } \Omega \text{ cm}$ . The metal-insulator (MI) transition at  $\sim 200 \text{ K}$  for the parent compound completely disappears for  $x = 0.1$ . At low temperatures, the resistivity value is about five orders of magnitude higher for  $x = 0.1$  than that of

the parent ( $x = 0.0$ ) compound. The  $\sigma_{dc}$  of these samples is explained using polaron hopping conduction mechanism<sup>5</sup> with an expression of the form

$$\sigma_{dc} = (\sigma_0/T) \exp(-W/k_B T) \quad (1)$$

where  $\sigma_0$  is a pre-exponential factor,  $W$  is the activation energy,  $k_B$  is the Boltzmann constant and  $T$  is the absolute measuring temperature. The Debye temperature ( $\theta_D$ ) of the samples decrease from 473 to 287 K with the increase of  $x$ . Density of states (DOS) at the Fermi level ( $N(E_F)$ ) is too observed to decrease from  $8.74 \times 10^{21}$  to  $2.20 \times 10^{20} \text{ eV}^{-1} \text{ cm}^{-3}$  with the increase of Al doping and is temperature ( $\theta_D$ ) of the samples decrease from 473 to 287 K with the increase of  $x$ . Density of states (DOS) at the Fermi level ( $N(E_F)$ ) is too observed to decrease from  $8.74 \times 10^{21}$  to  $2.20 \times 10^{20} \text{ eV}^{-1} \text{ cm}^{-3}$  with the increase of Al doping and



**Fig. 2.** Temperature dependence of resistivity of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) samples. is consistent with the increase of resistivity data. Activation energy ( $W$ ) determined from the slope of  $\log_{10}(\sigma_{dc}T)$  vs.  $10^3/T$  curve above the temperature of  $\theta_D/2$  is  $\sim 45 \text{ meV}$  for undoped sample and  $63 \text{ meV}$  for  $x=0.1$  sample. Polaron-hopping energy ( $W_h$ ) is calculated from the relation<sup>5</sup>

$$W = W_h + W_d/2 \text{ for } T > \theta_D/2 \quad (2)$$

where  $W_d$  is the disorder energy arising due to the energy difference of the neighboring sites and is significant at very low temperature ( $T < \theta_D/4$ ). At high temperature, the activation energy is mainly contributed by  $W_h$ . The values of  $W_h$  calculated at a temperature of 290 K are 45 and 50 meV for  $x = 0.0$  and  $0.1$  samples respectively. These findings are in accordance with the reported literature.<sup>6</sup> From Holstein's relation<sup>7</sup>, the polaron bandwidth is given by

$$J \approx 0.67 \text{ } h\nu_{ph} (T/\theta_D)^{1/4}, \quad (3)$$

$$\text{where, } H = (2k_B T W_h / \pi)^{1/4} (h\nu_{ph} / \pi)^{1/2} \quad (4)$$

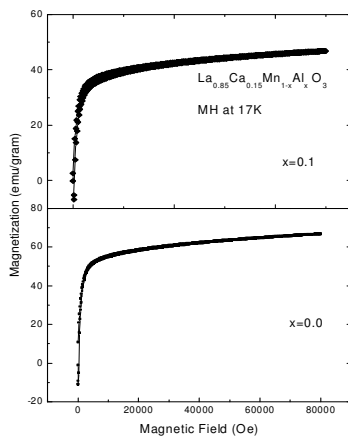
$\nu_{ph}$  is taken as  $10^{13} \text{ Hz}$  for both the samples. The values obtained at 290K for  $H$  are 18.60 and 14.89 meV,  $J \sim 23.89$  and  $27.00 \text{ meV}$ ,  $W_h/3 \sim 15.00$  and  $16.93$  for  $x = 0.0$  and  $0.1$  samples respectively. Since the value of  $J > W_h/3$ , it indicates the presence of large polaron hopping (LPH) in the LCMAO samples. The values of

polaron coupling constant ( $\gamma_p$ ), which is a measure of electron-phonon (e-ph) interaction in these manganites<sup>5</sup> varies from 2.22 for undoped sample to 4.15 in Al doped sample. Hence, the e-ph interaction seems to be weak in undoped sample, however strong coupling is observed in case of doped sample. This fact is further confirmed using the relation<sup>5</sup>

$$m_p = m^* \exp(\gamma_p) \quad (5)$$

where,  $m_p$  is the polaron mass and  $m^*$  is the rigid lattice effective mass. From the calculated values of  $\exp(\gamma_p)$  (9.20 for undoped and 64.00 for doped sample), it is clear that strong e-ph interaction is present in Al doped sample. Therefore, it may be concluded that adiabatic large polaron hopping conduction of carriers with strong e-ph interaction is responsible for the dc conductivity of Al substituted LCMAO sample.

Figure 3 shows the M-H curves of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) samples. The decrease of magnetization with Al doping concentration is



**Fig.3.** Magnetization versus magnetic field (M-H) curve for Al doped  $\text{La}_{0.85}\text{Ca}_{0.15}\text{Mn}_{1-x}\text{Al}_x\text{O}_3$  ( $x = 0.0$  and  $0.1$ ) at a temperature of 17K.

confirmed by the field dependent magnetization at a constant temperature of 17 K. Both of the samples show ferromagnetic behavior. The decrease in magnetization in Al substituted sample can be understood taking into account the fact that Al will increase the distance between the Mn ions causing certain degree of distortion in Mn sublattice, responsible for ferromagnetic interactions.

## Conclusions

This study shows that Al doping increases the resistivity in LCMAO sample suppressing the metal insulator transition of  $\text{La}_{0.85}\text{Ca}_{0.15}\text{MnO}_3$  (undoped) compound. Conduction in Al substituted sample takes place by large polarons in adiabatic region with strong e-ph coupling. Magnetization decreases with the increase of Al ion which is consistent with non magnetic nature of  $\text{Al}^{3+}$ .

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